

~~A1~~
the component ratio "x" of Al is in a range of $0.3 \leq x \leq 1.0$, so that said semiconductor laser light emitting device is configured as an index guide type semiconductor laser light emitting device.

A2
9. (Once amended) A semiconductor laser light emitting device comprising:
a stacked film composed of a stack of group III nitride semiconductor films each containing at least one kind selected from aluminum, gallium, indium, and boron;
wherein,
an upper portion of said stacked film is formed into a ridge-like stripe, to form a current injection region;
a current injection width W_{st} of said current injection region is in a range of $1 \mu m \leq W_{st} \leq 3 \mu m$;
a current non-injection region formed on both sides of said ridge-like stripe;
at least part of said current non-injection region is made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0 \leq x \leq 1.0$); and
the component ratio "x" of Al is in a range of $0.15 < x < 0.30$, so that said semiconductor laser light emitting device is configured as a weak index type pulsation semiconductor laser light emitting device.

A3
17. (Once amended) A semiconductor laser light emitting device comprising:
a stacked film composed of a stack of group III nitride semiconductor films each containing at least one kind selected from aluminum, gallium, indium, and boron;